

L Number	Hits	Search Text	DB	Time stamp
4	633	(359/223).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 08:11
5	304	(359/298).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 08:16
6	581	(359/838).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 08:23
7	88	(205/116).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 08:27
8	422	((bulk or (single near3 crystal\$) or homogen\$) near3 silicon) and (internal with (mirror or reflect\$))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 09:34
9	71	((((bulk or (single near3 crystal\$) or homogen\$) near3 silicon) and (internal with (mirror or reflect\$)))) and anisotrop\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 08:31
10	5	((bulk or (single near3 crystal\$) or homogen\$) near3 silicon) and (internal\$2 with (mirror or reflect\$) with etch\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 09:02
11	1	((bulk or (single near3 crystal\$) or homogen\$) near3 silicon) and (atom\$6 with flat with (mirror or reflect\$) with etch\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 09:04
12	6	((bulk or (single near3 crystal\$) or homogen\$) near3 silicon) and (atom\$6 with flat with (mirror or reflect\$))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 09:07
13	0	((bulk or (single near3 crystal\$) or homogen\$) near3 silicon) and (atom\$6 with flat with anisotrop\$)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 09:08

14	2	silicon same (atom\$6 with flat with anisotrop\$)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 09:10
15	5	silicon same (atom\$6 with flat) same anisotrop\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 09:10
16	512	((bulk or (single near3 crystal\$) or homogen\$) near3 silicon) and ((internal or bur\$3) with (mirror or reflect\$))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 09:13
17	356	((((bulk or (single near3 crystal\$) or homogen\$) near3 silicon) and ((internal or bur\$3) with (mirror or reflect\$))) and etch\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 09:14
18	69	((((bulk or (single near3 crystal\$) or homogen\$) near3 silicon) and ((internal or bur\$3) with (mirror or reflect\$))) and (etch\$4 with plane)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 09:14
19	166	((bulk or crystal\$ or homogen\$) near3 silicon) and (internal with (mirror or reflect\$ or deflect\$)) and anisotrop\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 10:15
21	324	((bulk or crystal\$ or homogen\$) near3 silicon) and (integra\$ with (mirror or reflect\$ or deflect\$)) and anisotrop\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 11:13
22	7	("4182544" "4657339" "4669817" "4674828" "4675521" "4684208" "4705349").PN.	USPAT	2003/07/30 11:04
23	642	silicon and (integra\$ with (mirror or reflect\$ or deflect\$)) and (anisotrop\$ with etch\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 11:16
24	182	(integra\$ with (mirror or reflect\$ or deflect\$)) and (silicon with anisotrop\$ with etch\$3) and (hole or bore or passage)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 11:56
25	84	(silicon with (mirror or reflect\$ or deflect\$) with (micromachin\$ or micro?machin\$)) and (anisotrop\$ with etch\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 11:58

26	35	(atom\$6 near3 (smooth\$4 or flat\$4)) with etch\$4 with silicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 12:25
27	256	(atom\$6 near3 (smooth\$4 or flat\$4)) and (mirror or reflect\$ or deflect\$) and etch\$4 and silicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 12:26
28	35	((atom\$6 near3 (smooth\$4 or flat\$4)) same (mirror or reflect\$ or deflect\$)) and etch\$4 and silicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 12:31
29	52	(atom\$6 near3 (smooth\$4 or flat\$4)) and (mirror or reflect\$ or deflect\$) and (anisotrop\$ with etch\$4) and silicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 12:32
-	2	("6008128").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 09:09
-	576	(359/223).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/07 17:14
-	255	(359/298).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/07 17:14
-	505	(359/838).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/07 17:14
-	88	(205/116).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/07 17:15
-	135	((359/223).CCLS.) and silicon\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 09:20

-	85	((359/298).CCLS.) and silicon\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 10:21
-	66	((359/838).CCLS.) and silicon\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 10:30
-	8	((205/116).CCLS.) and silicon\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 10:33
-	421	silicon and mirror and bulk and monolith\$ and crystal\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 10:43
-	46	(silicon and mirror and bulk and monolith\$ and crystal\$4) and inlet and outlet	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 10:37
-	31	silicon and mirror and bulk and monolith\$ and (crystal\$4 adj plane)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 10:51
-	89	(single adj crystal adj silicon) and mirror and (crystal\$4 adj plane)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 08:28
-	692	(single adj crystal adj silicon) and mirror and plane and etch\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 11:43
-	309	((single adj crystal adj silicon) and mirror and plane and etch\$3) and anisotrop\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 11:09
-	101	((single adj crystal adj silicon) and mirror and plane and etch\$3) and anisotrop\$) and fiber and optic\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 11:10

-	121	(single and crystal and silicon) and mirror and plane and etch\$3 and anisotrop\$ and fiber and optic\$4 and internal\$2	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 14:11
-	256	singl and crystal\$4 and silicon and mirror and etch\$3 and stripe and intersect\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 14:25
-	118	(single and crystal\$4 and silicon and mirror and etch\$3 and stripe and intersect\$4) and internal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 11:58
-	373	(single near crystal\$4 near silicon) with mirror	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 12:05
-	39	((single near crystal\$4 near silicon) with mirror) and (fiber near optic\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 12:06
-	3645	digital and mirror and device and silicon and crystal\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 14:12
-	168	(digital and mirror and device and silicon and crystal\$4) and bulk and monolith\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 14:12
-	341	silicon and mirror and etch\$3 and stripe and intersect\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 14:36
-	2259	silicon and mirror and pattern\$3 and anisotrop\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 14:37
-	403	(single adj crystal\$4 adj silicon) and mirror and pattern\$3 and anisotrop\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 15:20

-	0	(bulk with (single adj crystal\$4 adj silicon)) and (mirror near pattern\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 15:22
-	20	silicon and (mirror near pattern\$3) and (anisotrop\$ near etch\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 15:34
-	16	silicon and ((mirror near pattern\$3) with array\$)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 15:39
-	2585	(mirror with array\$) and silicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 16:16
-	9	(mirror with array\$) and (bulk with single with crystal\$4 with silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 15:43
-	2	((mirror with array\$) and silicon) and anisotrop\$ and (bulk near crystal\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 15:44
-	2	monolithic adj bulk adj crystal adj silicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 16:17
-	2	monolithic with bulk with crystal with silicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 16:17
-	1586	monolithic and bulk and crystal and silicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 16:18
-	25	(monolithic and bulk and crystal and silicon) and (crystalline near plane)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 16:19

-	362	(monolithic and bulk and crystal and silicon) and (crystalline and plane)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 16:20
-	4	((monolithic and bulk and crystal and silicon) and (crystalline and plane)) and (micro?mirror or (micro adj mirror))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 16:20
-	109	((monolithic and bulk and crystal and silicon) and (crystalline and plane)) and mirror	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 16:41
-	4	silicon near mirror near array	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 16:42
-	1415	digital near (micromirror or micro?mirror or (micro adj mirror)) near device	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 16:43
-	350	(digital near (micromirror or micro?mirror or (micro adj mirror)) near device) and silicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 17:12
-	16	(digital near (micromirror or micro?mirror or (micro adj mirror)) near device) and (single adj crystal adj silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 17:14
-	3991	(mirror or reflect\$) and (single adj crystal adj silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 17:16
-	240	((mirror or reflect\$) and (single adj crystal adj silicon)) and bulk and monolith\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 17:42
-	148	anisotrop\$ with silicon with array with etch\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 17:43

-	226	(anisotrop\$ with silicon with process\$) and (mirror or refl ctor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 18:38
-	25	silicon and mirror and passage and (crystalline adj plane)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 18:42
-	42	(monolithic and bulk and crystal and silicon) and (mirror or reflector) and crystalline and plane and intersect\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 18:44
-	606	(359/223).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 08:10
-	290	(359/298).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 08:10
-	553	(359/838).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 08:10
-	88	(205/116).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 08:10
-	42	((359/223).CCLS.) and (mirror or reflector) and anisotrop\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/07 17:28
-	23	((359/298).CCLS.) and (mirror or reflector) and anisotrop\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/07 17:52
-	15	((359/838).CCLS.) and (mirror or reflector) and anisotrop\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/07 17:54

-	1	((205/116).CCLS.) and (mirror or reflector) and anisotrop\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/07 17:56
-	244	silicon and ((mirror or refl ctor) with anisotrop\$)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/10 08:20
-	2	westra.in. and silicon and anisotrop\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/10 08:21
-	101	westra.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/10 08:21